

## MBR30H35PT thru MBR30H60PT

Vishay General Semiconductor

## **Dual Common-Cathode Schottky Rectifier**

High Barrier Technology for Improved High Temperature Performance



PIN 2 PIN 1 O-► PIN 3 O CASE

PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	30 A				
V <sub>RRM</sub>	35 V to 60 V				
I <sub>FSM</sub>	200 A				
V <sub>F</sub>	0.58 V, 0.63 V				
I <sub>R</sub>	150 μA				
T <sub>J</sub> max.	175 °C				

## **FEATURES**

- · Guardring for overvoltage protection
- Lower power losses, high efficiency
- · Low forward voltage drop
- Low leakage current
- · High forward surge capability
- High frequency operation
- Solder dip 260 °C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

## **TYPICAL APPLICATIONS**

For use in low voltage, high frequency rectifier of switching mode power supplies, freewheeling diodes, dc-to-dc converters or polarity protection application.

## **MECHANICAL DATA**

Case: TO-247AD (TO-3P) Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test

## Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS (T <sub>A</sub> = 25 °C unless otherwise noted)								
PARAMETER	SYMBOL	MBR30H35PT	MBR30H45PT	MBR30H50PT	MBR30H60PT	UNIT		
Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	35	45	50	60	V		
Maximum working peak reverse voltage	V <sub>RWM</sub>	35	45	50	60	V		
Maximum DC blocking voltage	V <sub>DC</sub>	35	45	50	60	V		
Maximum average forward rectified current (Fig. 1)	I <sub>F(AV)</sub>	30						
Non-repetitive avalanche energy per diode at 25 °C, $I_{AS}$ = 4 A, L = 10 mH	E <sub>AS</sub>	80						
Peak forward surge current, 8.3 ms single half sine-wave superimposed on rated load per diode	I <sub>FSM</sub>	200						
Peak repetitive reverse surge current per diode <sup>(1)</sup>	I <sub>RRM</sub>	2.0 1.0			.0	А		
Peak non-repetitive reverse energy (8/20 µs waveform)	E <sub>RSM</sub>	30 20			0	mJ		
Electrostatic discharge capacitor voltage human body model: C = 100 pF, R = 1.5 $k\Omega$	V <sub>C</sub>	25						
Voltage rate of change at rated $V_R$	dV/dt	10 000						
Operating junction temperature range	ТJ	- 65 to + 175				°C		
Storage temperature range	T <sub>STG</sub>	- 65 to + 175				°C		

#### Note:

(1) 2.0  $\mu$ s pulse width, f = 1.0 kHz





RoHS

COMPLIANT

Vishay General Semiconductor



ELECTRICAL CHARACTERISTICS (T <sub>C</sub> = 25 °C unless otherwise noted)									
PARAMETER	TEST CONDITIONS		SYMBOL		MBR30H35PT MBR30H45PT		MBR30H50PT MBR30H60PT		
				TYP.	MAX.	TYP.	MAX.		
Maximum instantaneous forward voltage per diode <sup>(1)</sup>	$I_{F} = 20 \text{ A}$ $I_{F} = 20 \text{ A}$ $I_{F} = 30 \text{ A}$ $I_{F} = 30 \text{ A}$	T <sub>J</sub> = 25 °C T <sub>J</sub> = 125 °C T <sub>J</sub> = 25 °C T <sub>J</sub> =125 °C	V <sub>F</sub>	- 0.54 - 0.62	0.66 0.58 0.73 0.66	- 0.60 - 0.66	0.74 0.63 0.83 0.70	v	
Maximum reverse current at rated $\rm V_R$ per diode $^{(2)}$		T <sub>J</sub> = 25 °C T <sub>J</sub> = 125 °C	I <sub>R</sub>	- 6.0	150 25	- 4.0	150 25	μA mA	

#### Notes:

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width  $\leq$  40 ms

<b>THERMAL CHARACTERISTICS</b> (T <sub>A</sub> = 25 °C unless otherwise noted)								
PARAMETER	SYMBOL	MBR30H35PT MBR30H45PT MBR30H50PT MBR30H60		MBR30H60PT	UNIT			
Thermal resistance, junction to case per diode	$R_{ ext{ heta}JC}$	1.4				°C/W		

ORDERING INFORMATION (Example)								
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE			
TO-247AD	MBR30H45PT-E3/45	6.13	45	30/tube	Tube			

### **RATINGS AND CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25 °C unless otherwise specified)

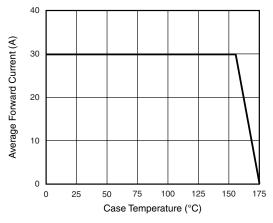
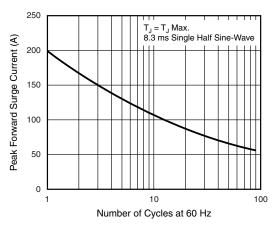
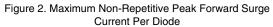


Figure 1. Forward Current Derating Curve







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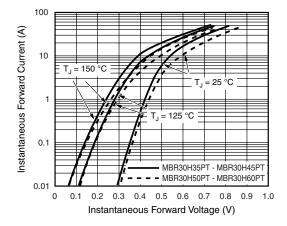


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

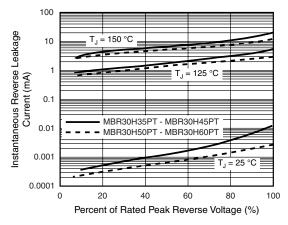


Figure 4. Typical Reverse Characteristics Per Diode

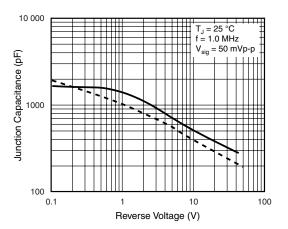


Figure 5. Typical Junction Capacitance Per Diode

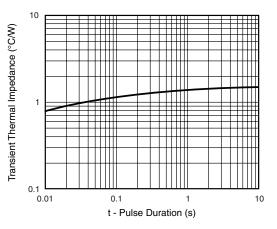
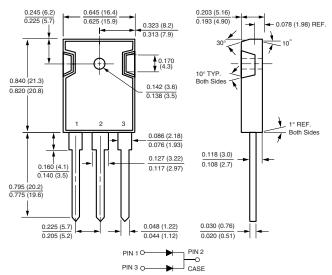


Figure 6. Typical Transient Thermal Impedance Per Diode

## **PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)

TO-247AD (TO-3P)





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# Disclaimer

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